

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the present application.

Listing of Claims:

Claim 1 (currently amended): A wafer holder for semiconductor manufacturing devices, the wafer holder comprising:
a sintered aluminum nitride (AlN) wafer holder body, the wafer holder body fabricated from AlN powder having an oxygen impurity concentration of 2 weight percent or less and a metal impurity concentration of 2000 parts per million or less;
the wafer holder body having a wafer-carrying surface;
an electrical circuit formed either on a surface other than the wafer-carrying surface of the wafer holder body, or else inside it; and
electrodes for supplying power to said electrical circuit, said electrodes being separated by an interval that is 10% or more of the thickness of the wafer holder body such that in use the wafer-carrying surface has a temperature uniformity of within ± 1 percent.

Claim 2 (original): The wafer holder set forth in claim 1, wherein one or more metals selected from the group consisting of tungsten, molybdenum and tantalum are incorporated into portions of said electrodes that are directly connected to said circuit.

Claim 3 (original): A semiconductor manufacturing device wherein the wafer holder set forth in claim 1 is installed.

Claim 4 (original): A semiconductor manufacturing device wherein the wafer holder set forth in claim 2 is installed.

Claim 5 (currently amended): A wafer holder for semiconductor manufacturing devices, the wafer holder comprising:

a sintered aluminum nitride (AlN) wafer holder body, the wafer holder body fabricated from AlN powder having an oxygen impurity concentration of 2 weight percent or less and a metal impurity concentration of 2000 parts per million or less;

the wafer holder body having a wafer-carrying surface;

a plurality of electrical circuits formed either on a surface other than the wafer-carrying surface of the wafer holder body, or else inside it; and

at least three electrodes for supplying power to said plurality of electrical circuits, each pair of electrodes being separated by an interval that is 10% or more of the thickness of the wafer holder body, such that in use the wafer-carrying surface has a temperature uniformity of within ± 1 percent.